Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough in Smal Signal (BISS) transitor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4360X

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_{C} and I_{CM}
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switches
- · Battery charger
- · LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-60	V
I _C	collector current			-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-6	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	225	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



60 V, 3 A PNP low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		C
2	С	collector		В—
3	В	base	3 2 1	- N
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5360X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5360X	S42

60 V, 3 A PNP low VCEsat (BISS) transistor

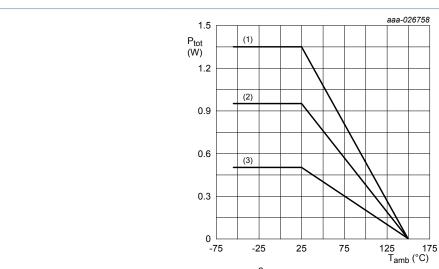
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134)

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-80	V
V_{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-6	Α
I _B	base current			-	-500	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-1	Α
P _{tot}	total power dissipation		[1]	-	500	mW
			[2]	-	950	mW
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, single-sided copper, 6 cm²
- (2) FR4 PCB, single-sided copper, 1 cm²
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fr	thermal resistance in from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	132	K/W
			<u>[3]</u>	-	-	93	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

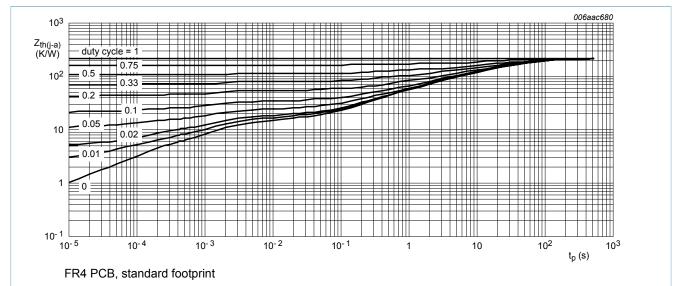


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

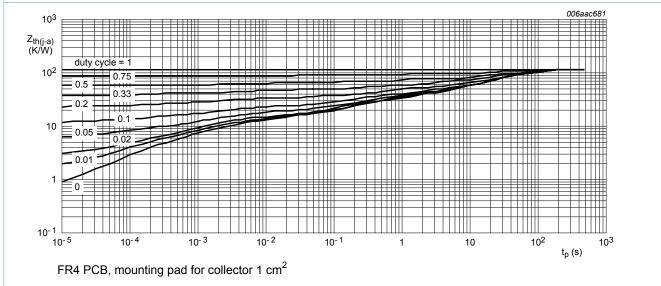
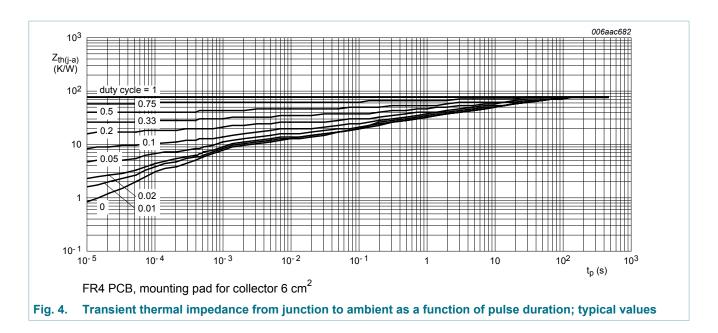


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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60 V, 3 A PNP low VCEsat (BISS) transistor

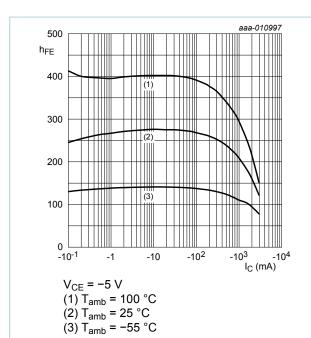
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-100	nA
	current	V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C		-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I_{C} = 0 A; T_{amb} = 25 °C		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -50 mA; T_{amb} = 25 °C		150	-	-	
		V_{CE} = -5 V; I_{C} = -500 mA; T_{amb} = 25 °C		130	-	-	
		V _{CE} = -5 V; I _C = -1 A; T _{amb} = 25 °C		120	-	-	
		V_{CE} = -5 V; I_{C} = -2 A; T_{amb} = 25 °C	[1]	100	-	-	
		V_{CE} = -5 V; I_{C} = -3 A; T_{amb} = 25 °C	[1]	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = -500 mA; I_B = -50 mA; T_{amb} = 25 °C		-	-	-150	mV
		I_C = -1 A; I_B = -100 mA; T_{amb} = 25 °C	[1]	-	-	-200	mV
		I_C = -2 A; I_B = -200 mA; T_{amb} = 25 °C	[1]	-	-	-450	mV
		I_C = -3 A; I_B = -300 mA; T_{amb} = 25 °C	[1]	-	-	-550	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	225	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -1 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	-	-	-1.1	V
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C		65	130	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	28	32	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

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DC current gain as a function of collector Fig. 5. current; typical values

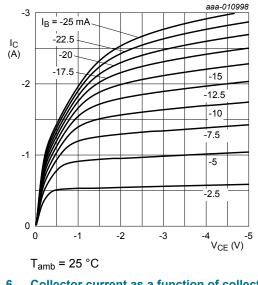
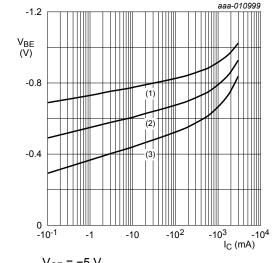


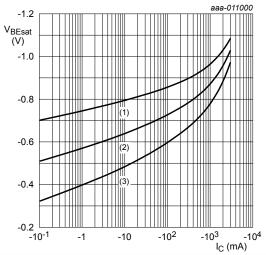
Fig. 6. Collector current as a function of collectoremitter voltage; typical values



 $V_{CE} = -5 V$ (1) $T_{amb} = -55 °C$

(2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values

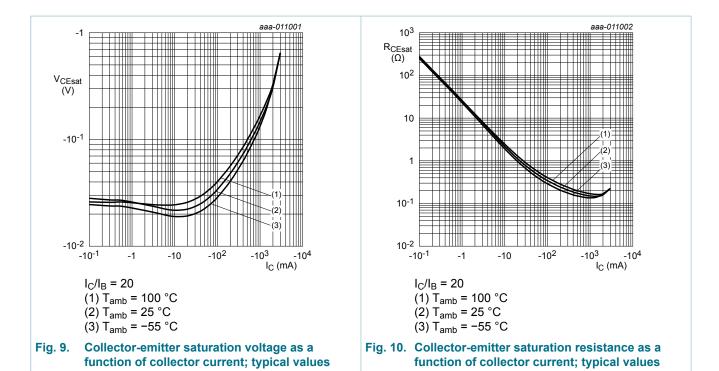


 $I_C/I_B = 20$ (1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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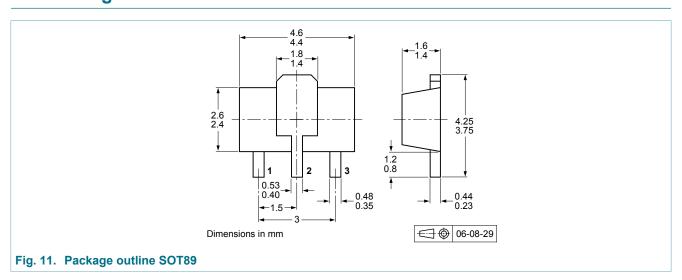


11. Test information

Quality information

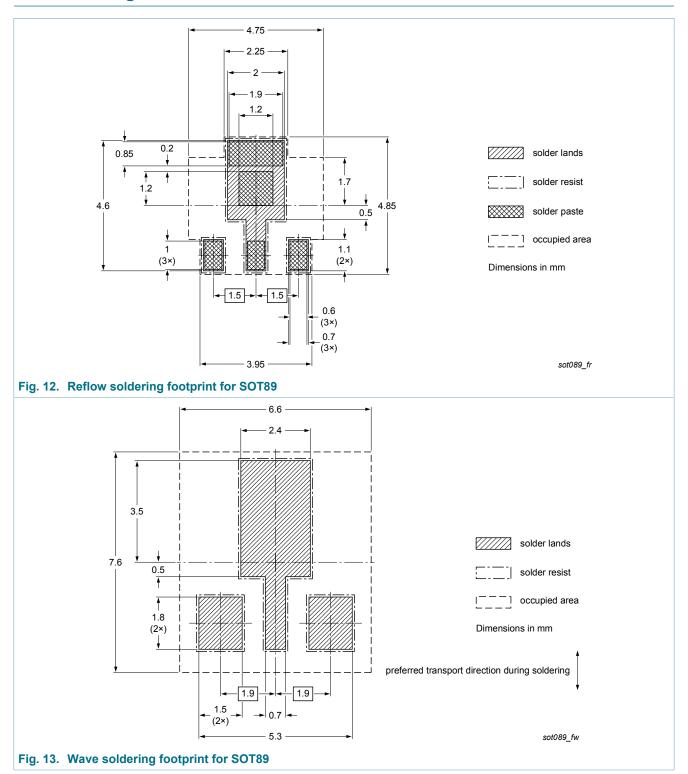
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5360X v.1	20170703	Product data sheet	-	-

60 V, 3 A PNP low VCEsat (BISS) transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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	Features and benefits

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